

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











Ultrafast recovery - high voltage diode

Main product characteristics

I _{F(AV)}	30 A
V _{RRM}	1000 V
Tj	175° C
V _F (typ)	1.30 V
t _{rr} (typ)	42 ns

Features and benefits

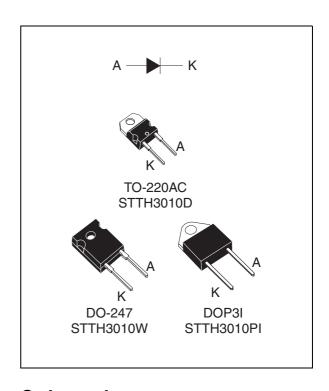
- Ultrafast, soft recovery
- Very low conduction and switching losses
- High frequency and/or high pulsed current operation
- High reverse voltage capability
- High junction temperature
- Insulated package:
 - DOP3I
 Electrical insulation = 2500 V_{RMS}
 Capacitance = 12 pF

Description

The high quality design of this diode has produced a device with low leakage current, regularly reproducible characteristics and intrinsic ruggedness. These characteristics make it ideal for heavy duty applications that demand long term reliability.

Such demanding applications include industrial power supplies, motor control, and similar mission-critical systems that require rectification and freewheeling. These diodes also fit into auxiliary functions such as snubber, bootstrap, and demagnetization applications.

The improved performance in low leakage current, and therefore thermal runaway guard band, is an immediate competitive advantage for this device.



Order codes

Part Number	Marking
STTH3010D	STTH3010D
STTH3010W	STTH3010W
STTH3010PI	STTH3010PI

Characteristics STTH3010

Characteristics 1

Absolute ratings (limiting values at 25° C, unless otherwise specified) Table 1.

Symbol	Pa	Value	Unit		
V_{RRM}	Repetitive peak reverse voltage	Repetitive peak reverse voltage			
I _{F(RMS)}	RMS forward current			50	Α
ı	Average forward current \$ 0.5	TO-220 / DO-247	T _c = 105° C	20	Α
$I_{F(AV)}$ Average forward current, $\delta = 0.5$	DOP3I	T _c = 65° C	30	A 	
I _{FRM}	Repetitive peak forward current	rd current $t_p = 5 \mu s$, $F = 5 kHz square$			Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$			180	Α
T _{stg}	Storage temperature range			-65 to + 175	°C
Tj	Maximum operating junction tempera	Maximum operating junction temperature			

Table 2. **Thermal parameters**

Symbol	Para	Value	Unit	
D	Junction to case	TO-220 / DO-247	1.1	°C/W
R _{th(j-c)}	Junction to case	DOP3I	1.8	C/VV

Table 3. Static electrical characteristics

Symbol	Parameter	Test co	nditions	Min.	Тур	Max.	Unit
I _B ⁽¹⁾	Reverse leakage current	T _j = 25° C	V- - V			15	μA
'R`	IR Preverse leakage current	T _j = 125° C	$V_R = V_{RRM}$		10	100	μΛ
		T _j = 25° C				2	
V _F ⁽²⁾	Forward voltage drop	T _j = 100° C	I _F = 30 A		1.4	1.8	V
		T _j = 150° C			1.3	1.7	

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2$ %

To evaluate the conduction losses use the following equation: P = 1.3 x $I_{F(AV)}$ + 0.013 $I_{F}^{2}_{(RMS)}$

$$P = 1.3 \times I_{F(AV)} + 0.013 I_{F^2(BMS)}$$

577

^{2.} Pulse test: t_p = 380 μ s, δ < 2 %

STTH3010 Characteristics

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
		$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$			100	
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -100 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		53	70	ns
	$I_F = 1 \text{ A, } dI_F/dt = -200 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		42	55		
I _{RM}	Reverse recovery current	$I_F = 30 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s}, \ V_R = 600 \text{ V}, T_j = 125^{\circ} \text{ C}$		24	32	Α
S	Softness factor	$I_F = 30 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s}, \ V_R = 600 \text{ V}, T_j = 125^{\circ} \text{ C}$		1		
t _{fr}	Forward recovery time	$I_F = 30 \text{ A}$ $dI_F/dt = 100 \text{ A/µs}$ $V_{FR} = 1.5 \text{ x } V_{Fmax}, T_j = 25^{\circ} \text{ C}$			450	ns
V _{FP}	Forward recovery voltage	$I_F = 30 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s},$ $T_j = 25^{\circ} \text{ C}$		5		V

Figure 1. Conduction losses versus average current

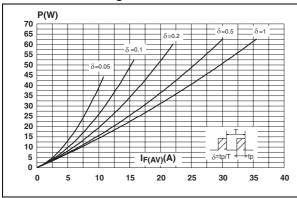


Figure 2. Forward voltage drop versus forward current

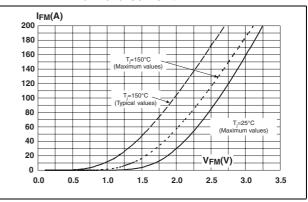


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

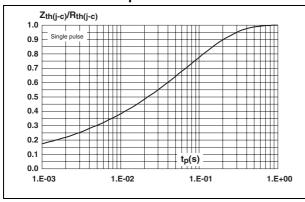
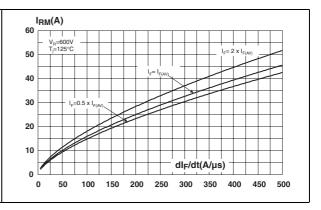


Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)



Characteristics STTH3010

Figure 5. Reverse recovery time versus dl_F/dt (typical values)

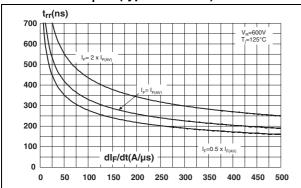


Figure 6. Reverse recovery charges versus dl_F/dt (typical values)

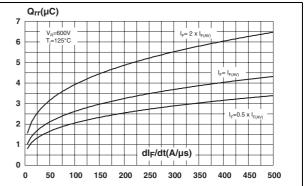


Figure 7. Softness factor versus dl_F/dt (typical values)

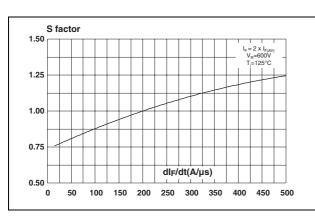
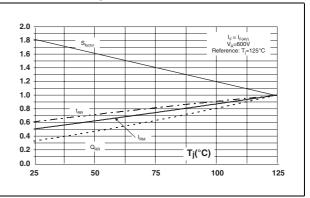


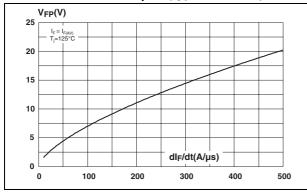
Figure 8. Relative variations of dynamic parameters versus junction temperature



STTH3010 Characteristics

Figure 9. Transient peak forward voltage versus dl_F/dt (typical values)

Figure 10. Forward recovery time versus dl_F/dt (typical values)



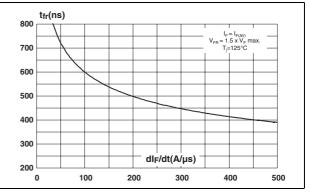
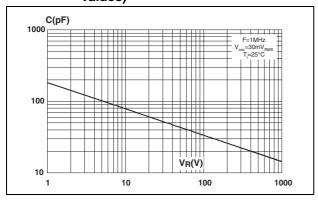


Figure 11. Junction capacitance versus reverse voltage applied (typical values)



5//

Package information STTH3010

2 Package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)

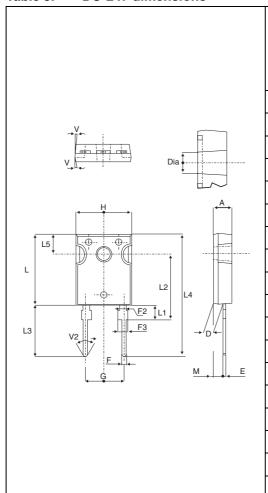
Recommended torque value: 0.55 Nm (TO-220AC)

Recommended torque value: 0.80 Nm (SOD93, DOP31, and DO-247)

Maximum torque value: 0.7 Nm (TO-220AC)

Maximum torque value: 1.0 Nm (SOD93, DOP31, and DO-247)

Table 5. DO-247 dimensions

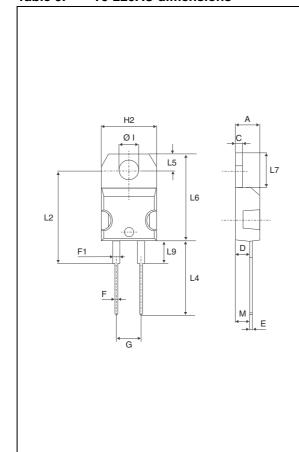


	DIMENSIONS					
REF.	Millimete		rs		Inches	
	Min.		Max	Min.		Max.
Α	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
Е	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
G		10.90			0.429	
Н	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
М	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

577

STTH3010 Package information

Table 6. T0-220AC dimensions

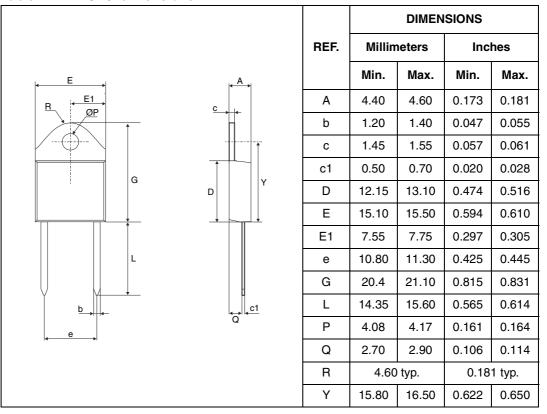


	DIMENSIONS				
REF.	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
Е	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024	0.034	
F1	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194	0.202	
H2	10.00	10.40	0.393	0.409	
L2	16.40) typ.	0.645 typ.		
L4	13.00	14.00	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
М	2.6 typ.		0.102	2 typ.	
Diam. I	3.75	3.85	0.147	0.151	

47/

Package information STTH3010

Table 7. DOP3I dimensions



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

8/10

3 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH3010D	STTH3010D	TO-220AC	1.86 g	50	Tube
STTH3010PI	STTH3010PI	DOP3I	4.46 g	30	Tube
STTH3010W	STTH3010W	DO-247	4.4 g	30	Tube

4 Revision history

Date	Revision	Description of Changes
02-Mar-2006	1	First issue.

577

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZE REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT DESIGNED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

47/